
41. (Amended) A device according to claim 32 wherein said semiconductor layer has an electron mobility of 15 to 300 cm²/Vsec.

E2

42. (Amended) A device according to claim 32 wherein said semiconductor layer has a hole mobility of 10 to 200 cm²/Vsec.

54. (Amended) A device according to claim 45 wherein said semiconductor layer has an electron mobility of 15 to 300 cm²/Vsec.

E3

55. (Amended) A device according to claim 45 wherein said semiconductor layer has a hole mobility of 10 to 200 cm²/Vsec.

Please add new claims 77-80 as follows.

77. A semiconductor device according to claim 1, wherein said semiconductor layer has an electron mobility of 15 to 300 cm²/Vsec.

E4

78. A semiconductor device according to claim 1, wherein said semiconductor layer has a hole mobility of 10 to 200 cm²/Vsec.

79. A semiconductor device according to claim 10, wherein said semiconductor layer has an electron mobility of 15 to 300 cm²/Vsec.

80. A semiconductor device according to claim 10, wherein said semiconductor layer has a hole mobility of 10 to 200 cm²/Vsec.
